



DMN2990UDJ

### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = 25°C
20V	0.99Ω @ V <sub>GS</sub> = 4.5V	450mA
	1.2Ω @ V <sub>GS</sub> = 2.5V	400mA
	1.8Ω @ V <sub>GS</sub> = 1.8V	330mA
	2.4Ω @ V <sub>GS</sub> = 1.5V	300mA

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- General Purpose Interfacing Switch
- **Power Management Functions**
- **DC-DC Converters**
- Analog Switch

Notes:

## **Features**

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package 1mm x 1mm
- Low Package Profile, 0.45mm Maximum Package Height
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMN2990UDJQ)

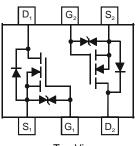
## **Mechanical Data**

- Case: SOT963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.027 grams (Approximate)





SOT963



Schematic and Transistor Diagram

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2990UDJ-7	SOT963	10K/Tape & Reel
DMN2990UDJ-7A	SOT963	10K/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

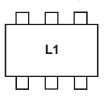
2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

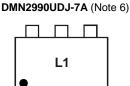
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information (Note 5 & 6)

### DMN2990UDJ-7 (Note 5)





L1 = Product Type Marking Code

5. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways). Notes: 6. Part number with suffix 7A designates devices marked with a Pin 1 indicator. There is no other difference between both devices.

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Top View



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 7) $V_{GS}$ = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	450 350	mA
Continuous Drain Current (Note 7) V <sub>GS</sub> = 1.8V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	330 220	mA
Pulsed Drain Current (Note 8)			I <sub>DM</sub>	800	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	PD	350	mW
Thermal Resistance, Junction to Ambient	R <sub>0</sub> JA	360	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

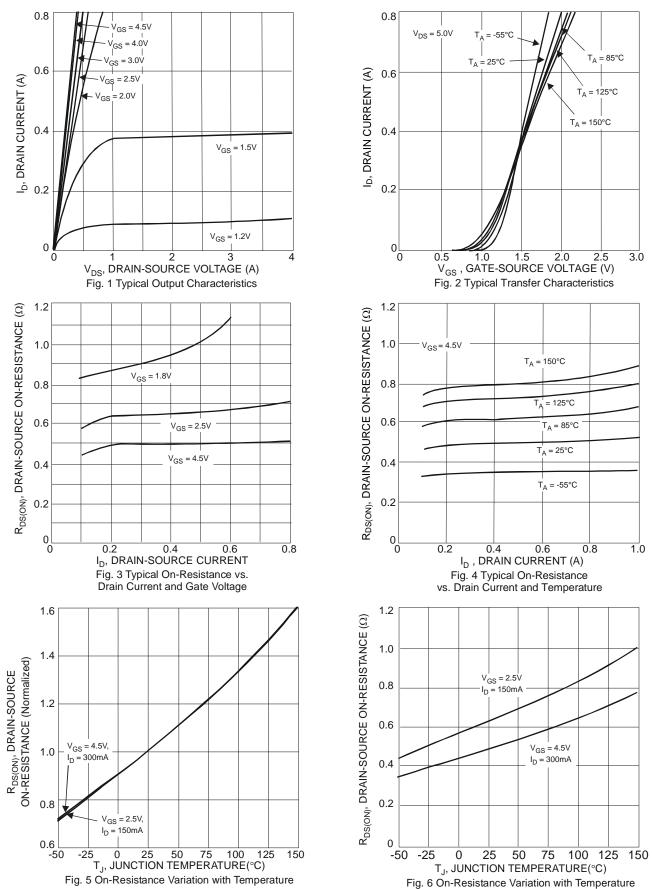
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zana Oata Maltana Duala Ormani @T		-	-	50	nA	$V_{DS} = 5V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C	IDSS	-	-	100		$V_{DS} = 16V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	-					-	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	-	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		-	0.60	0.99		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100mA	
		-	0.75	1.2	Ω	$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	0.90	1.8		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 20mA	
		-	1.2	2.4		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA	
		-	2.0	-		$V_{GS} = 1.2V, I_D = 1mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	180	-	-	ms	$V_{DS} = 10V, I_D = 400mA$	
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	-	0.6	1.0	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	-	27.6	-	pF		
Output Capacitance	C <sub>oss</sub>	-	4.0	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	2.8	-	pF	1 = 1.00012	
Total Gate Charge	Qg	-	0.5	-	nC		
Gate-Source Charge	Q <sub>gs</sub>	-	0.07	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 250mA$	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.07	-	nC	ID = 250 IIA	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.0	-	ns		
Turn-On Rise Time	t <sub>R</sub>	-	3.3	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	19.0	-	ns	$R_L = 47\Omega, R_g = 10\Omega,$	
Turn-Off Fall Time	t <sub>F</sub>	-	6.4	-	ns	$-I_D = 200 \text{mA}$	

Notes: 7. Device mounted on FR-4 PCB, with minimum recommended pad layout.

B. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

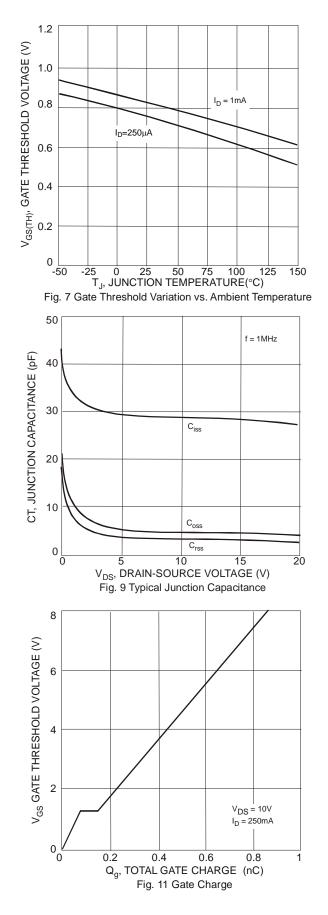


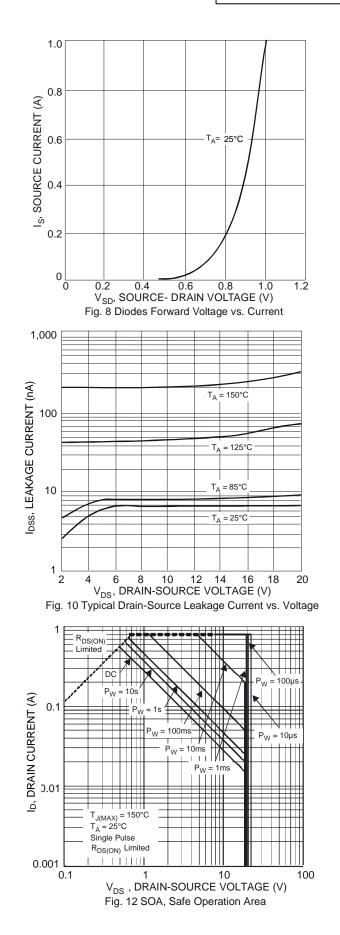
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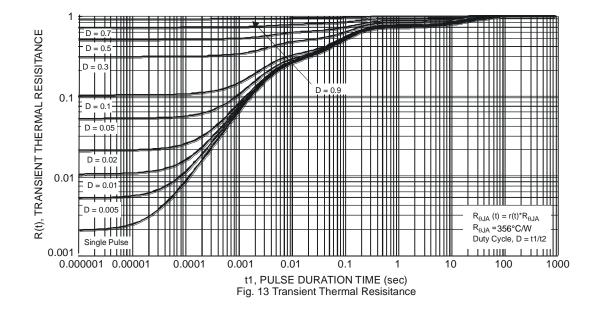
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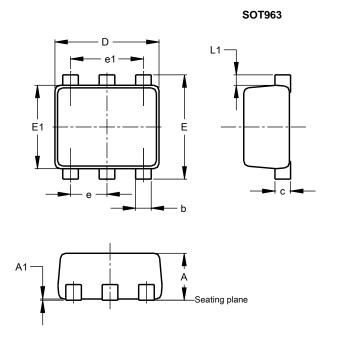






## **Package Outline Dimensions**

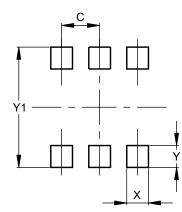
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT963						
Dim	Min	Max	Тур			
Α	0.40	0.50	0.45			
A1	0.00	0.05				
b	0.10	0.20	0.15			
С	0.120	0.180	0.150			
D	0.95	1.05	1.00			
Е	0.95	1.05	1.00			
E1	0.75	0.85	0.80			
е			0.35			
e1			0.70			
L1	0.05	0.15	0.10			
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.350
Х	0.200
Ŷ	0.200
Y1	1.100

SOT963



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